



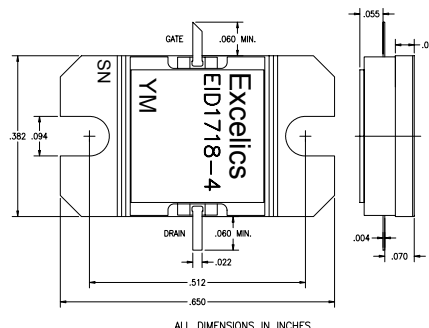
EID1718-4

17.30-18.10 GHz 4-Watt Internally-Matched Power FET

Issued Date: 12/16/03

FEATURES

- 17.30-18.10 GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +36.0 dBm Output Power at 1dB Compression
- 6.0 dB Power Gain at 1dB Compression
- 25% Power Added Efficiency
- Hermetic Metal Flange Package



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P_{1dB}	Output Power at 1dB Compression $f = 17.30\text{-}18.10\text{GHz}$ $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 1200\text{mA}$	35.5	36.0		dBm
G_{1dB}	Gain at 1dB Compression $f = 17.30\text{-}18.10\text{GHz}$ $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 1200\text{mA}$	5.0	6.0		dB
ΔG	Gain Flatness $f = 17.30\text{-}18.10\text{GHz}$ $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 1200\text{mA}$			± 0.6	dB
PAE	Power Added Efficiency at 1dB Compression $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 1200\text{mA}$ $f = 17.30\text{-}18.10\text{GHz}$		25		%
I_{d1dB}	Drain Current at 1dB Compression $f = 17.30\text{-}18.10\text{GHz}$		1300	1800	mA
IM3	Output 3rd Order Intermodulation Distortion $\Delta f = 5\text{ MHz}$ 2-Tone Test; $P_{out} = 30.0\text{ dBm S.C.L.}^2$ $V_{DS} = 10\text{ V}$, $I_{DSQ} \approx 65\% I_{DSS}$ $f = 18.10\text{GHz}$	-29.0	-34.0		dBc
I_{DSS}	Saturated Drain Current $V_{DS} = 3\text{ V}$, $V_{GS} = 0\text{ V}$		2080	2880	mA
V_P	Pinch-off Voltage $V_{DS} = 3\text{ V}$, $I_{DS} = 20\text{ mA}$		-2.5	-4.0	V
R_{TH}	Thermal Resistance ³		4.5	5.5	$^\circ\text{C/W}$

1. Tested with 100 Ohm gate resistor.
2. S.C.L. = Single Carrier Level.
3. Overall R_{th} depends on case mounting.

ABSOLUTE MAXIMUM RATINGS FOR CONTINUOUS OPERATION^{1,2}

SYMBOL	CHARACTERISTIC	VALUE
V_{DS}	Drain to Source Voltage	10 V
V_{GS}	Gate to Source Voltage	-4.5 V
I_{DS}	Drain Current	I_{DSS}
I_{GSF}	Forward Gate Current	40 mA
P_{IN}	Input Power	@ 3dB compression
P_T	Total Power Dissipation	23.0 W
T_{CH}	Channel Temperature	150 $^\circ\text{C}$
T_{STG}	Storage Temperature	-65/+150 $^\circ\text{C}$

1. Operating the device beyond any of the above ratings may result in permanent damage or reduction of MTTF.
2. Bias conditions must also satisfy the following equation $P_T < (T_{CH} - T_{PKG})/R_{TH}$; where T_{PKG} = temperature of package, and $P_T = (V_{DS} * I_{DS}) - (P_{OUT} - P_{IN})$.

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